**TOSHIBA 1SS321** 

## TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

# 1 S S 3 2 1

#### LOW VOLTAGE HIGH SPEED SWITCHING.

Low Forward Voltage :  $V_F = 0.42V$  (Typ.)

Low Reverse Current : IR=500nA (Max.)

Small Package : SC-59 (SOT-23MOD)

### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Maximum (Peak) Reverse Voltage	$v_{ m RM}$	12	V	
Reverse Voltage	$V_{\mathbf{R}}$	10	V	
Maximum (Peak) Forward Current	$I_{ extbf{FM}}$	150 (*)	mA	
Average Forward Current	IO	50 (*)	mA	
Surge Current (t=10ms)	$I_{FSM}$	1000 (*)	mA	
Power Dissipation	P	150	mW	
Junction Temperature	$T_{ m j}$	125	°C	
Storage Temperature Range	$ m T_{stg}$	<b>−</b> 55 <b>~</b> 125	°C	

Unit in mm + 0.5 2.5 – 0.3 + 0.25 1.5 – 0.15 ANODE 1 ANODE 2 CATHODE 1, 2 S-MINI **JEDEC** TO-236MOD **EIAJ** SC-59 TOSHIBA 1-3G1F

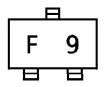
Weight: 0.012g

(\*) Unit Rating. Total Rating=Unit Rating×1.5.

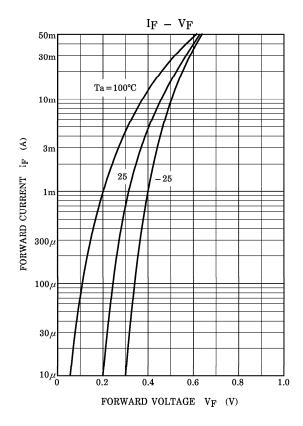
#### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

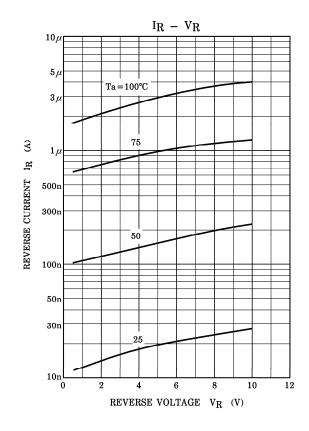
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CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V <sub>F (1)</sub>	I <sub>F</sub> =1mA	_	0.32	_	V
	$V_{F(2)}$	$I_{\mathbf{F}} = 10$ mA	_	0.42		
	$V_{F(3)}$	$I_{ m F}\!=\!50{ m mA}$	_	0.63	1.00	
Reverse Current	${ m I_R}$	$V_R = 10V$	_	_	500	nA
Total Capacitance	$\mathrm{C}_{\mathrm{T}}$	$V_R=0$ , f=1MHz	_	3.2	4.5	рF

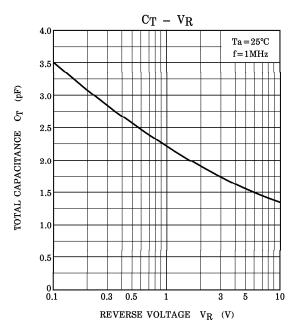
MARKING



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